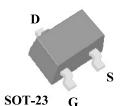
**▼** Simple Drive Requirement

- **▼** Small Package Outline
- **▼** Surface Mount Device
- **▼** RoHS Compliant & Halogen-Free

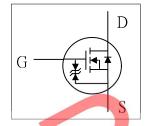


I <sub>D</sub>	450mA		
R <sub>DS(ON)</sub>	$2\Omega$		
BV <sub>DSS</sub>	60V		

### **Description**

Advanced Power MOSFETs utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

The SOT-23 package is universally used for all commercial-industrial applications.



**Absolute Maximum Ratings** 

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	٧
$V_{GS}$	Gate-Source Voltage	<u>+</u> 20	٧
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current <sup>3</sup> , V <sub>GS</sub> @ 10V	450	mA
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current <sup>3</sup> , V <sub>GS</sub> @ 10V	360	mA
I <sub>DM</sub>	Pulsed Drain Current <sup>1</sup>	950	mA
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation	0.7	W
	Linear Derating Factor	0.005	W/°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	$^{\circ}\!\mathbb{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^{\circ}\mathbb{C}$

### **Thermal Data**

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient <sup>3</sup>	180	°C/W

# Electrical Characteristics@T<sub>j</sub>=25°C(unless otherwise specified)

Parameter	Test Conditions	Min.	Тур.	Max.	Units
Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	-	-	V
Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	ı	0.06	-	۷/°C
Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =450mA	ı	-	2	Ω
	V <sub>GS</sub> =4.5V, I <sub>D</sub> =200mA		-	4	Ω
Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{D}=250$ uA	1	-	2.5	V
Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =450mA	ı	400	-	mS
Drain-Source Leakage Current	$V_{DS}$ =60V, $V_{GS}$ =0V	1		10	uA
Drain-Source Leakage Current (T <sub>j</sub> =70°C)	V <sub>DS</sub> =48V ,V <sub>GS</sub> =0V	1		100	uA
Gate-Source Leakage	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V		1	<u>+</u> 30	uA
Total Gate Charge <sup>2</sup>	I <sub>D</sub> =450mA	1	7	1.6	nC
Gate-Source Charge	V <sub>DS</sub> =50V		0.5	-	nC
Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	1	0.5	-	nC
Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =30V		12	_	ns
Rise Time	I <sub>D</sub> =450mA		10	-	ns
Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	56	-	ns
Fall Time	$R_D=52\Omega$	ı	29	-	ns
Input Capacitance	V <sub>GS</sub> =0V	1	32	50	pF
Output Capacitance	V <sub>DS</sub> =25V	-	8	-	pF
Reverse Transfer Capacitance	f=1.0MHz	-	6	-	pF
	Drain-Source Breakdown Voltage  Breakdown Voltage Temperature Coefficient  Static Drain-Source On-Resistance <sup>2</sup> Gate Threshold Voltage  Forward Transconductance  Drain-Source Leakage Current  Drain-Source Leakage Current (T <sub>j</sub> =70°C)  Gate-Source Leakage  Total Gate Charge <sup>2</sup> Gate-Source Charge  Gate-Drain ("Miller") Charge  Turn-on Delay Time <sup>2</sup> Rise Time  Turn-off Delay Time  Fall Time  Input Capacitance  Output Capacitance	$\begin{array}{llllllllllllllllllllllllllllllllllll$	$\begin{array}{c} \text{Drain-Source Breakdown Voltage} & V_{\text{GS}} = 0\text{V, I}_{\text{D}} = 250\text{uA} & 60 \\ \\ \text{Breakdown Voltage Temperature Coefficient} & \text{Reference to } 25^{\circ}\text{C}, \text{ I}_{\text{D}} = 1\text{mA} & - \\ \\ \text{Static Drain-Source On-Resistance}^2 & V_{\text{GS}} = 10\text{V, I}_{\text{D}} = 450\text{mA} & - \\ \\ V_{\text{GS}} = 4.5\text{V, I}_{\text{D}} = 200\text{mA} & - \\ \\ \text{Cate Threshold Voltage} & V_{\text{DS}} = V_{\text{GS}}, \text{ I}_{\text{D}} = 250\text{uA} & 1 \\ \\ \text{Forward Transconductance} & V_{\text{DS}} = 10\text{V, I}_{\text{D}} = 450\text{mA} & - \\ \\ \text{Drain-Source Leakage Current} & V_{\text{DS}} = 60\text{V, V}_{\text{GS}} = 0\text{V} & - \\ \\ \text{Drain-Source Leakage Current} & V_{\text{DS}} = 60\text{V, V}_{\text{GS}} = 0\text{V} & - \\ \\ \text{Cate-Source Leakage} & V_{\text{GS}} = \pm 20\text{V, V}_{\text{DS}} = 0\text{V} & - \\ \\ \text{Cate-Source Charge} & V_{\text{DS}} = 450\text{mA} & - \\ \\ \text{Gate-Source Charge} & V_{\text{DS}} = 50\text{V} & - \\ \\ \text{Gate-Drain ("Miller") Charge} & V_{\text{GS}} = 4.5\text{V} & - \\ \\ \text{Turn-on Delay Time}^2 & V_{\text{DS}} = 30\text{V} & - \\ \\ \text{Rise Time} & I_{\text{D}} = 450\text{mA} & - \\ \\ \text{Turn-off Delay Time} & R_{\text{G}} = 3.3  \Omega_{\text{V}} \text{V}_{\text{GS}} = 10\text{V} & - \\ \\ \text{Fall Time} & R_{\text{D}} = 52  \Omega & - \\ \\ \text{Input Capacitance} & V_{\text{GS}} = 0\text{V} & - \\ \\ \text{Output Capacitance} & V_{\text{DS}} = 25\text{V} & - \\ \\ \end{array}$	$\begin{array}{c} \text{Drain-Source Breakdown Voltage} & V_{\text{GS}} = 0\text{V}, \ I_{\text{D}} = 250\text{uA} & 60 & - \\ \\ \text{Breakdown Voltage Temperature Coefficient} & \text{Reference to } 25^{\circ}\text{C}, \ I_{\text{D}} = 1\text{mA} & - & 0.06 \\ \\ \text{Static Drain-Source On-Resistance}^2 & V_{\text{GS}} = 10\text{V}, \ I_{\text{D}} = 450\text{mA} & - & - \\ \hline V_{\text{CS}} = 4.5\text{V}, \ I_{\text{D}} = 250\text{uA} & 1 & - \\ \\ \text{Forward Transconductance} & V_{\text{DS}} = 10\text{V}, \ I_{\text{D}} = 450\text{mA} & - & 400 \\ \\ \text{Drain-Source Leakage Current} & V_{\text{DS}} = 60\text{V}, \ V_{\text{GS}} = 0\text{V} & - & - \\ \\ \text{Drain-Source Leakage Current} & V_{\text{DS}} = 60\text{V}, \ V_{\text{DS}} = 0\text{V} & - & - \\ \\ \text{Drain-Source Leakage Current} & V_{\text{DS}} = 48\text{V}, \ V_{\text{GS}} = 0\text{V} & - & - \\ \\ \text{Cate-Source Leakage} & V_{\text{CS}} = \pm 20\text{V}, \ V_{\text{DS}} = 0\text{V} & - & - \\ \\ \text{Total Gate Charge}^2 & I_{\text{D}} = 450\text{mA} & - & 1 \\ \\ \text{Gate-Source Charge} & V_{\text{DS}} = 50\text{V} & - & 0.5 \\ \\ \text{Gate-Drain} ("Miller") \text{ Charge} & V_{\text{DS}} = 30\text{V} & - & 0.5 \\ \\ \text{Gate-Drain} ("Miller") \text{ Charge} & V_{\text{DS}} = 30\text{V} & - & 12 \\ \\ \text{Rise Time} & I_{\text{D}} = 450\text{mA} & - & 10 \\ \\ \text{Turn-onf Delay Time} & R_{\text{C}} = 3.3\Omega, \text{V}_{\text{GS}} = 10\text{V} & - & 56 \\ \\ \text{Fall Time} & R_{\text{D}} = 52\Omega & - & 29 \\ \\ \text{Input Capacitance} & V_{\text{GS}} = 25\text{V} & - & 32 \\ \\ \text{Output Capacitance} & V_{\text{DS}} = 25\text{V} & - & 8 \\ \\ \end{array}$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

## Source-Drain Diode

	Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
$V_{SD}$		Forward On Voltage <sup>2</sup>	I <sub>S</sub> =450mA, V <sub>GS</sub> =0V	-	-	1.2	<

### Notes:

- 1. Pulse width limited by Max. junction temperature.
- 2 Pulse test
- 3.Surface mounted on 1 in 2 copper pad of FR4 board  $t \le 10 \text{sec}$ ;  $400^{\circ}\text{C/W}$  when mounted on min. copper pad.

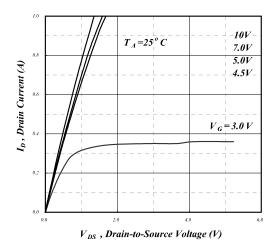
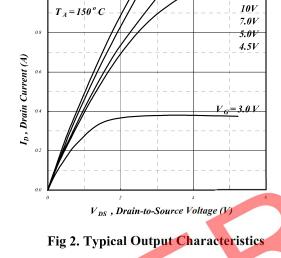


Fig 1. Typical Output Characteristics



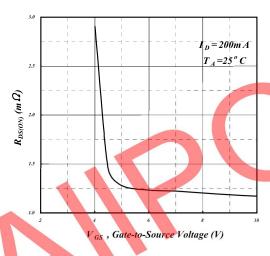


Fig 3. On-Resistance v.s. Gate Voltage

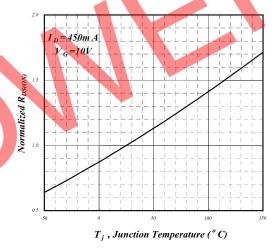


Fig 4. Normalized On-Resistance v.s. Junction Temperature

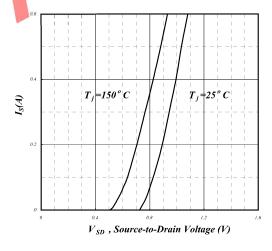


Fig 5. Forward Characteristic of Reverse Diode

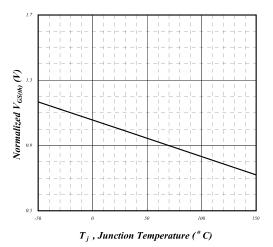


Fig 6. Gate Threshold Voltage v.s.
Junction Temperature

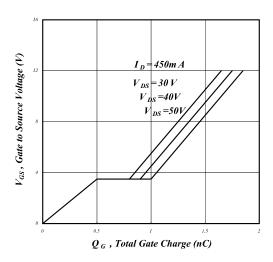


Fig 7. Gate Charge Characteristics

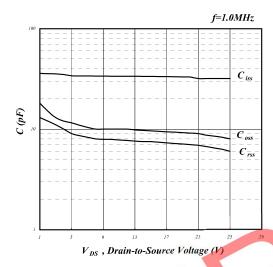


Fig 8. Typical Capacitance Characteristics

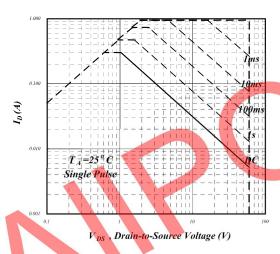


Fig 9. Maximum Safe Operating Area

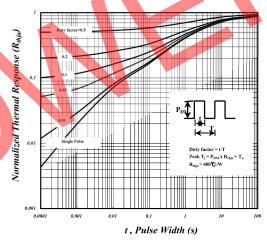


Fig 10. Effective Transient Thermal Impedance

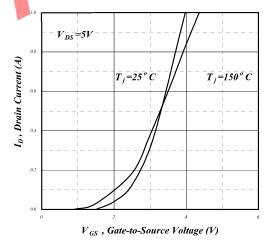


Fig 11. Transfer Characteristics

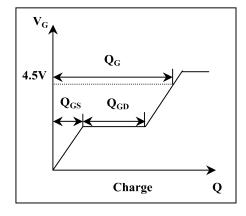


Fig 12. Gate Charge Waveform

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